



Dual P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)	
	0.101 at V _{GS} = - 4.5 V	- 4.5 ^a		
- 20	0.141 at V _{GS} = - 2.5 V	- 4.5 ^a	4.9 nC	
	0.192 at V _{GS} = - 1.8 V	- 2		

FEATURES

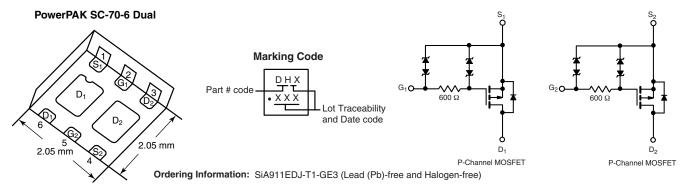
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- New Thermally Enhanced PowerPAK[®] SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
- Typical ESD Protection 4000 V



ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

 Load Switch, PA Switch and Battery Switch for Portable Devices



Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	- 20	V	
Gate-Source Voltage		V _{GS}	± 8		
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C T _C = 70 °C	L	- 4.5 ^a - 4.5 ^a		
	T _A = 25 °C T _A = 70 °C	I _D	- 3.6 ^{b, c} - 2.9 ^{b, c}	A	
Pulsed Drain Current		I _{DM}	- 10		
Continuous Source-Drain Diode Current	$T_C = 25 ^{\circ}C$ $T_A = 25 ^{\circ}C$	I _S	- 4.5 ^a - 1.6 ^{b, c}	7	
Maximum Power Dissipation	$T_C = 25 ^{\circ}\text{C}$ $T_C = 70 ^{\circ}\text{C}$	P _D	7.8 5	w	
Maximum Fower Dissipation	$T_A = 25 ^{\circ}\text{C}$ $T_A = 70 ^{\circ}\text{C}$, n	1.9 ^{b, c} 1.2 ^{b, c}		
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 150	°C		
Soldering Recommendations (Peak Temperature	· ·	260			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	52	65	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	12.5	16]	

Notes:

- a. Package limited.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 5.s
- d. See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under Steady State conditions is 110 °C/W.

SiA911EDJ

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 20			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = - 250 μA		- 21		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	1 _D = - 230 μΛ		2.1			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$			- 1	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	μΑ	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V		- 1			
		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			- 10	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 10			Α	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 2.7 A		0.083	0.101		
		$V_{GS} = -2.5 \text{ V}, I_D = -2.3 \text{ A}$		0.115	0.141	Ω	
		V _{GS} = - 1.8 V, I _D = - 1 A		0.153	0.192	1	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 2.7 A		7		S	
Dynamic ^b					I.		
Total Cata Charge		$V_{DS} = -10 \text{ V}, V_{GS} = -8 \text{ V}, I_{D} = -3.6 \text{ A}$		7.1	11	T	
Total Gate Charge	Q _g	V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 3.6 A		4.2	6.5	nC	
Gate-Source Charge	Q _{gs}			0.7			
Gate-Drain Charge	Q_{gd}			1.2			
Gate Resistance	R_g	f = 1 MHz		600		Ω	
Turn-On Delay Time t _{d(c}				92	140		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 3.5 Ω		200	300	ns	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 2.9 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		700	1100		
Fall Time	t _f			400	600		
Turn-On Delay Time	t _{d(on)}			32	50		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 3.5 Ω		70	105		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 2.9 A, V_{GEN} = - 8 V, R_g = 1 Ω		990	1500		
Fall Time	t _f			410	615		
Drain-Source Body Diode Characterist	ics			•			
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 4.5	A	
Pulse Diode Forward Current	I _{SM}				- 10		
Body Diode Voltage	V_{SD}	I _S = - 2.9 A, V _{GS} = 0 V		- 0.9	- 1.2	V	

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

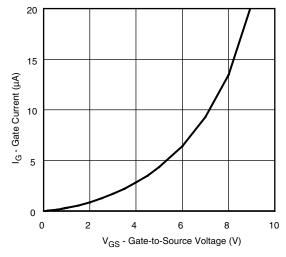
a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

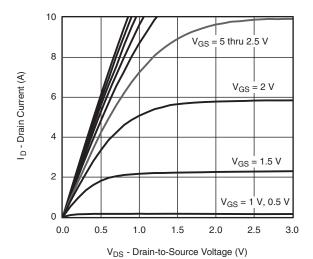




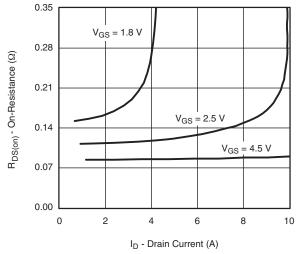
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



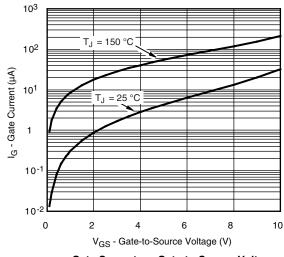
Gate Current vs. Gate-to-Source Voltage



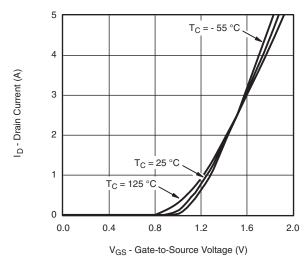
Output Characteristics



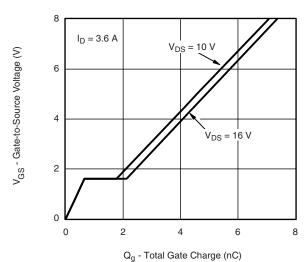
On-Resistance vs. Drain Current and Gate Voltage



Gate Current vs. Gate-to-Source Voltage



Transfer Characteristics



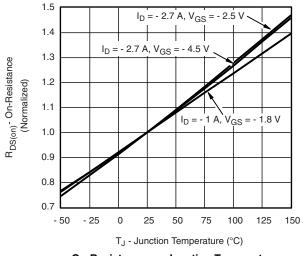
Gate Charge

Document Number: 68927 S09-0389-Rev. B, 09-Mar-09

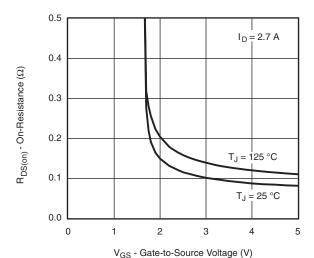
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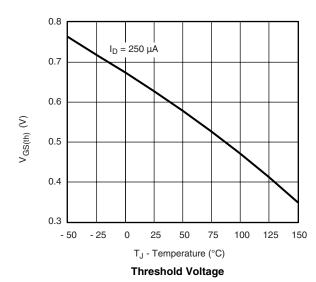
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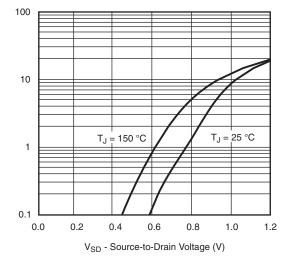


On-Resistance vs. Junction Temperature



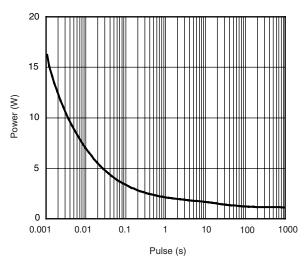
On-Resistance vs. Gate-to-Source Voltage



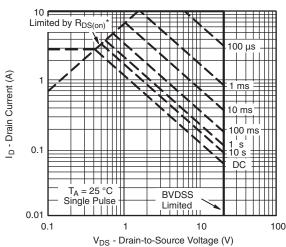


S - Source Current (A)

Soure-Drain Diode Forward Voltage



Single Pulse Power, Junction-to-Ambient



* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

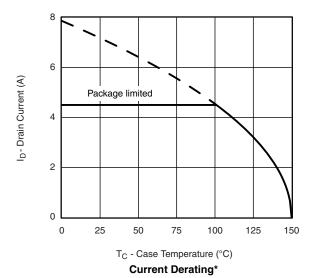
Safe Operating Area, Junction-to-Ambient

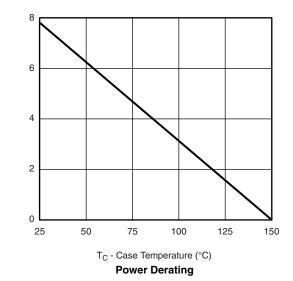




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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Power Dissipation (W)

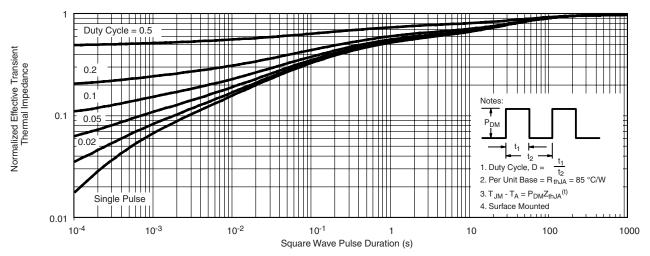
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^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package

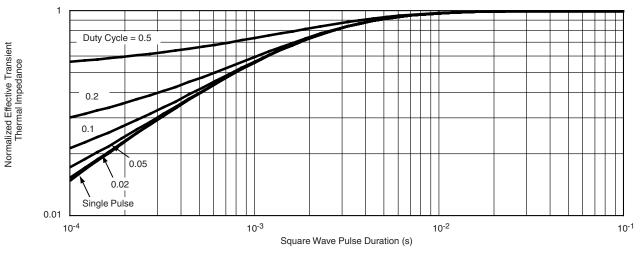
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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